

Supplementary Information

Combinatorial synthesis and characterization of thin film $\text{Al}_{1-x}\text{RE}_x\text{N}$ ($\text{RE} = \text{Pr}^{3+}$ and Tb^{3+}) heterostructural alloys

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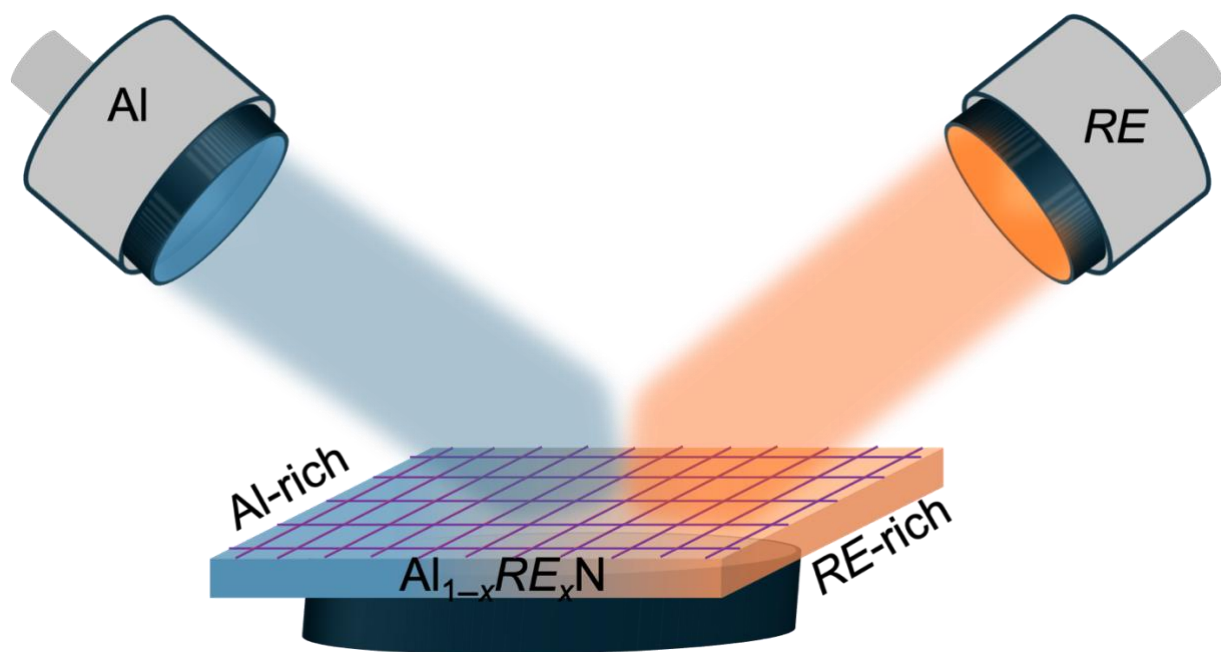


Figure S1: Magnetron sputtering schematic for the high throughput combinatorial synthesis showing a compositional gradient from Al-rich to RE-rich regions of the film.

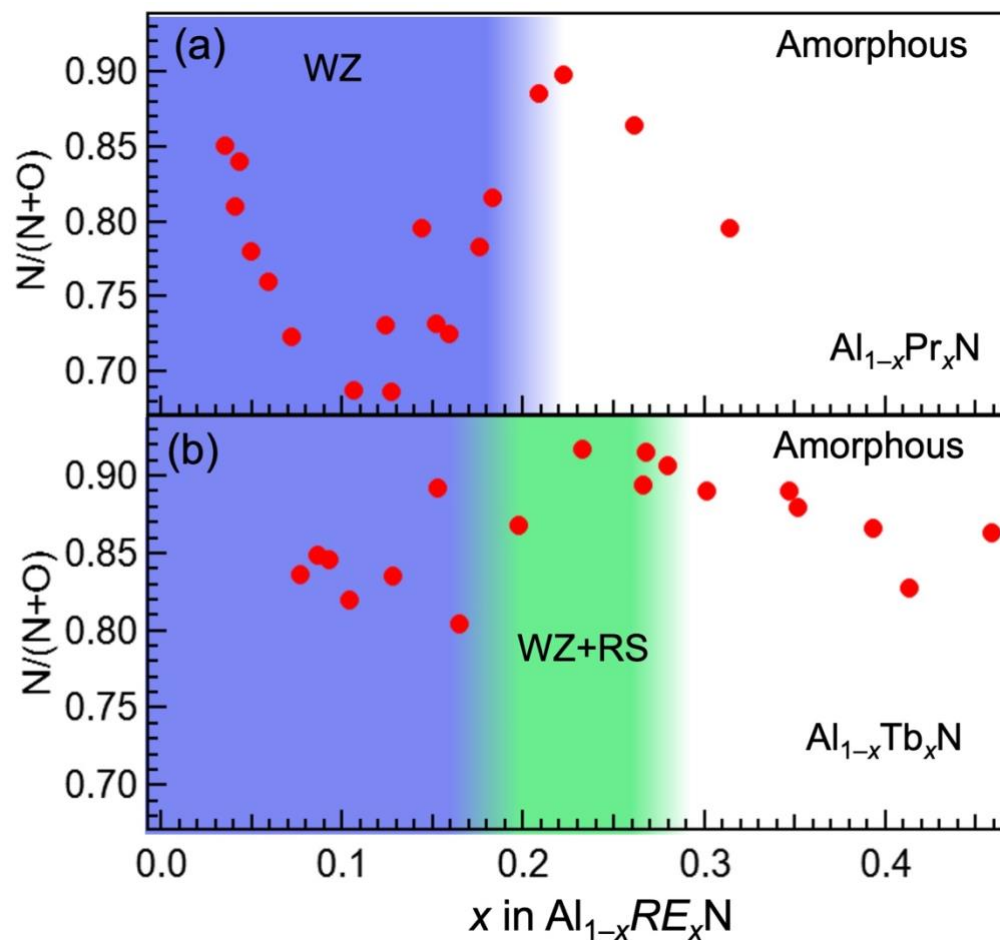


Figure S2: (a,b) Nitrogen composition vs. *RE* composition (*x*) measured with EPMA for (a) Al_{1-x}Pr_xN and (b) Al_{1-x}Tb_xN films across all detected phases.

Table S1: Comparison of overall stoichiometry and nitrogen composition extracted from STEM-EDS and EPMA

	EDS (near substrate)	EDS (surface)	EPMA
Al _{0.94} Pr _{0.06} N N/(N+O)	Al _{0.94} Pr _{0.06} N _{0.92} O _{0.08} 0.92	Al _{0.94} Pr _{0.06} N _{0.49} O _{0.23} 0.68	Al _{0.94} Pr _{0.06} N _{0.98} O _{0.30} 0.76
Al _{0.85} Pr _{0.15} N N/(N+O)	Al _{0.85} Pr _{0.27} N _{0.87} O _{0.05} 0.94	Al _{0.85} Pr _{0.25} N _{0.91} O _{0.23} 0.80	Al _{0.86} Pr _{0.14} N _{0.97} O _{0.25} 0.73
Al _{0.92} Tb _{0.08} N N/(N+O)	Al _{0.91} Tb _{0.07} N _{0.93} O _{0.04} 0.96	Al _{0.92} Tb _{0.07} N _{0.8} O _{0.15} 0.84	Al _{0.91} Tb _{0.08} N _{0.96} O _{0.17} 0.83
Al _{0.79} Tb _{0.21} N N/(N+O)	Al _{0.75} Tb _{0.23} N _{0.86} O _{0.15} 0.85	Al _{0.76} Tb _{0.2} N _{0.78} O _{0.35} 0.68	Al _{0.76} Tb _{0.23} N _{0.97} O _{0.09} 0.90

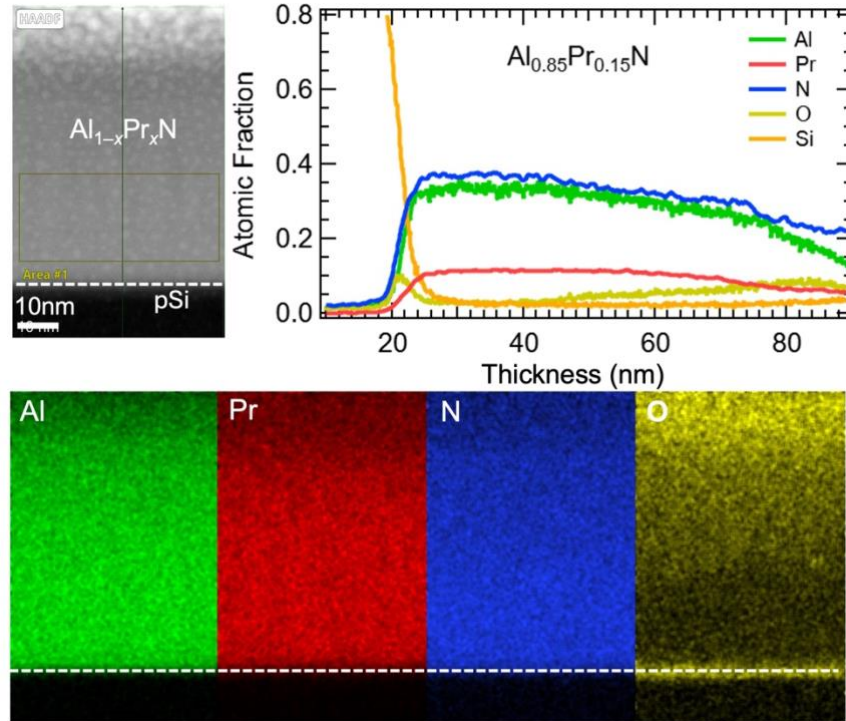


Figure S3: STEM-HAADF image and EDS elemental mapping at the Al *K*-peak, Pr *L*-peak, N *K*-peak, and O *K*-peak for $\text{Al}_{0.85}\text{Pr}_{0.15}\text{N}$ on a pSi substrate, along with the EDS atomic % line profile.

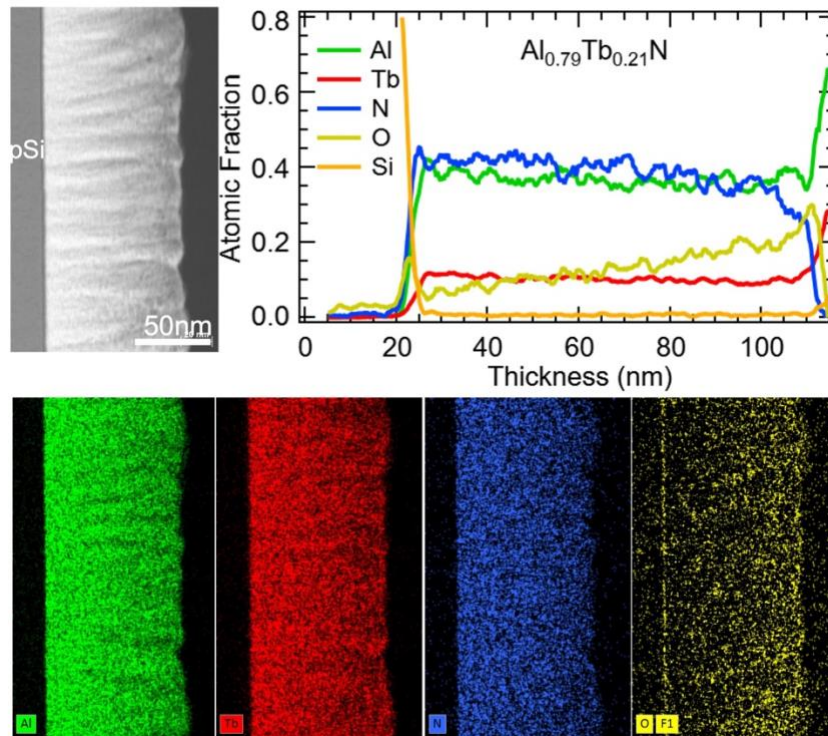


Figure S4: STEM-HAADF image and EDS elemental mapping at the Al *K*-peak, Tb *L*-peak, N *K*-peak, and O *K* peak for $\text{Al}_{0.79}\text{Tb}_{0.21}\text{N}$ on a pSi substrate, along with the EDS atomic % line profile.

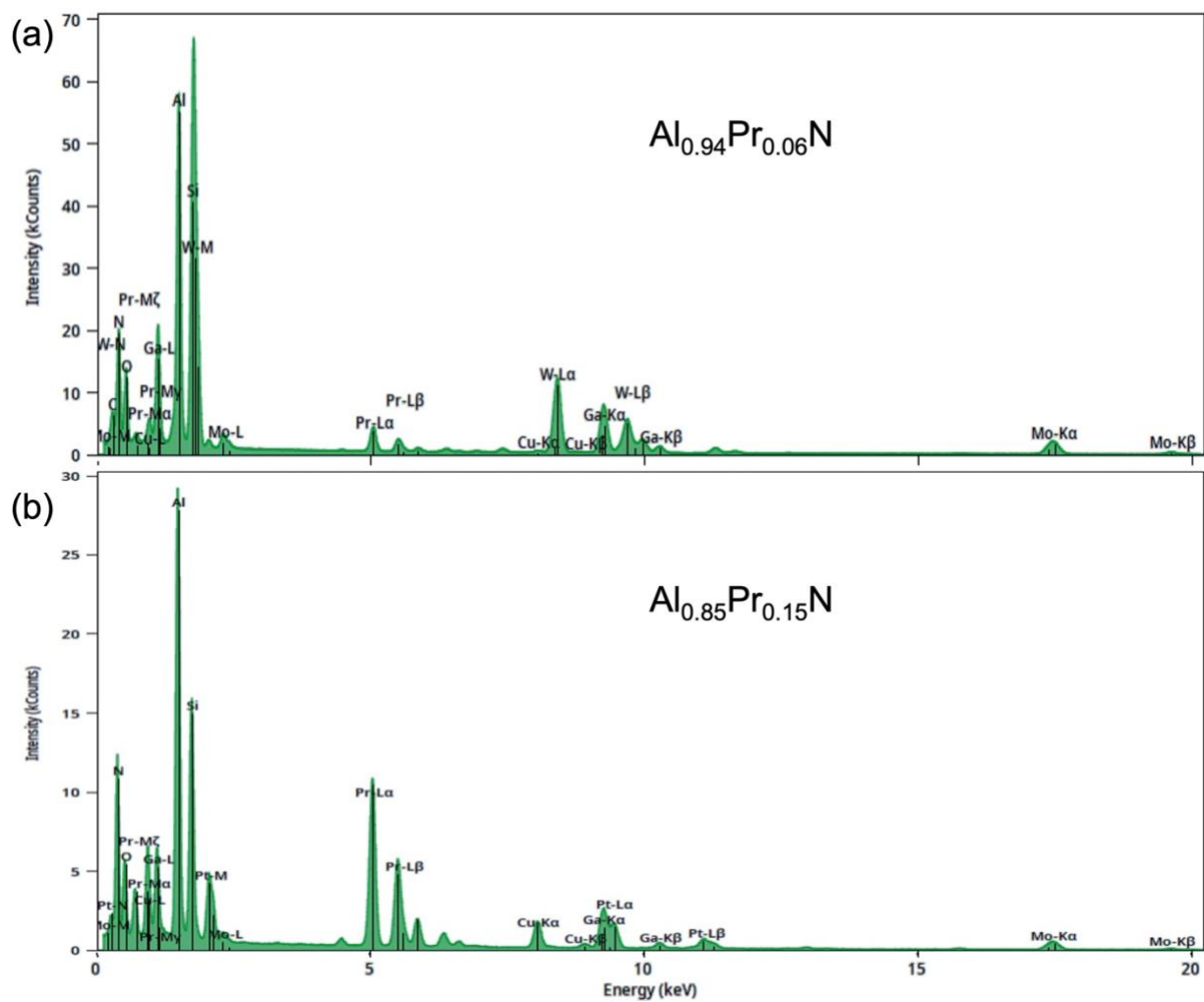


Figure S5: STEM-EDS spectra from (a) $\text{Al}_{0.94}\text{Pr}_{0.06}\text{N}$ and (b) $\text{Al}_{0.85}\text{Pr}_{0.15}\text{N}$ films on pSi substrates, collected over the whole map area. The $\text{Al}_{0.94}\text{Pr}_{0.06}\text{N}$ film was prepared with a W protective layer in the FIB, while Pt was used for the $\text{Al}_{0.85}\text{Pr}_{0.15}\text{N}$ film. Mo and Cu are extraneous signals from the TEM sample holder and Ga is from the FIB processing.

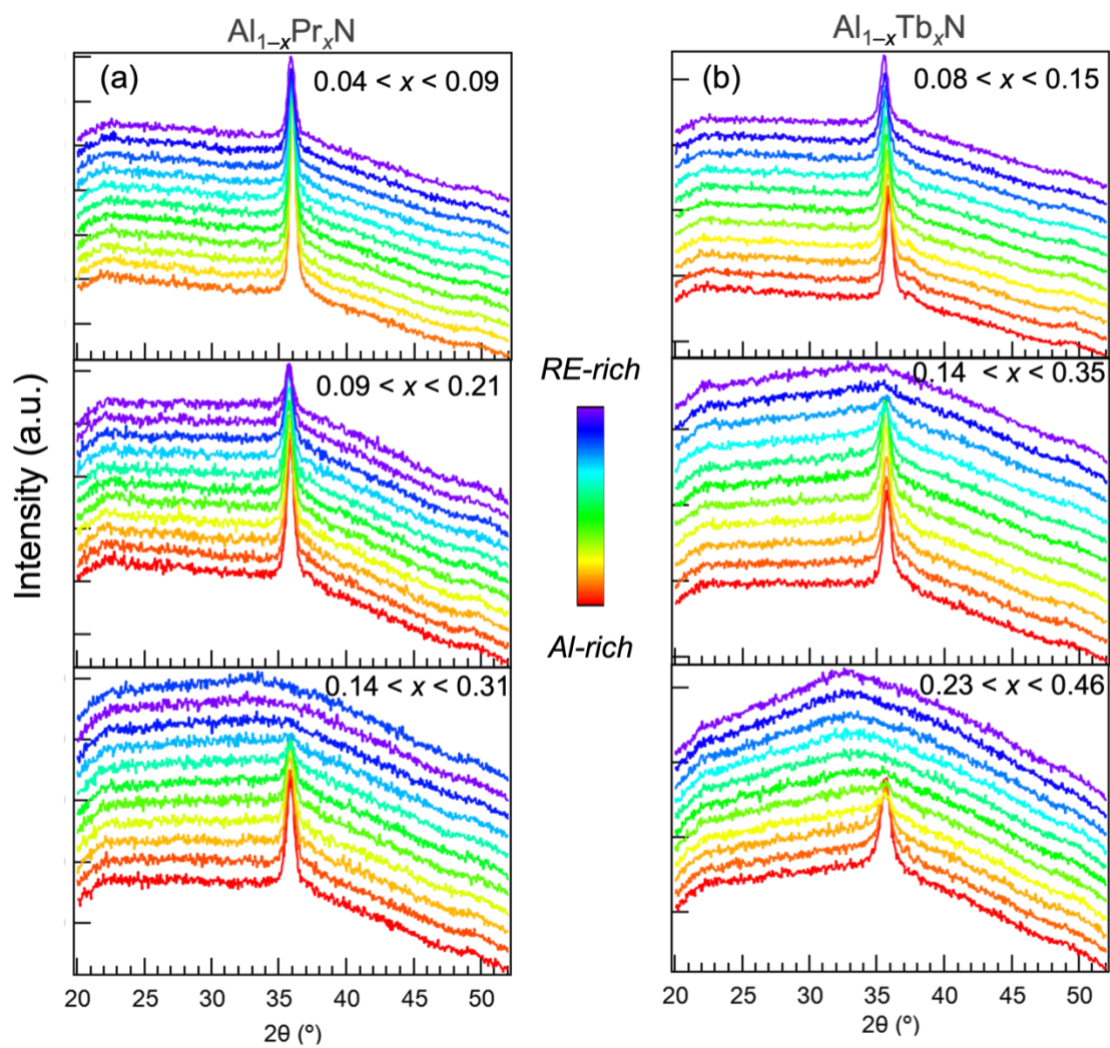


Figure S6: Lab XRD data of (a) $\text{Al}_{1-x}\text{Pr}_x\text{N}$ films with x from 0.04 to 0.31 and (b) $\text{Al}_{1-x}\text{Tb}_x\text{N}$ films with x from 0.08 to 0.46.

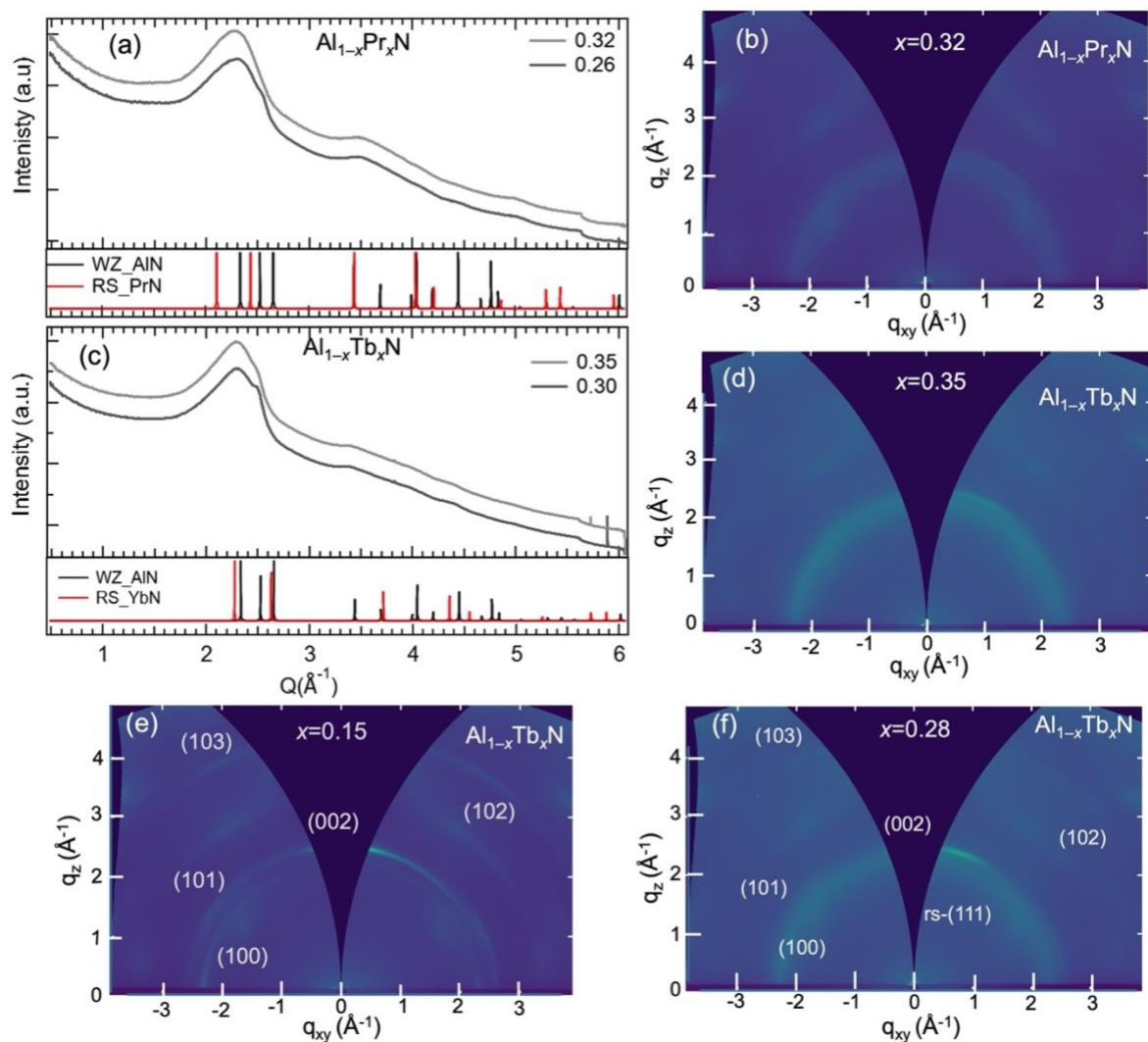


Figure S7: (a,c) Integrated GIWAXS patterns of two amorphous points in (a) $\text{Al}_{1-x}\text{Pr}_x\text{N}$ and (c) $\text{Al}_{1-x}\text{Tb}_x\text{N}$. (b,d) The 2D detector images of one of the amorphous points of (b) $\text{Al}_{1-x}\text{Pr}_x\text{N}$ ($x \approx 0.32$) and (d) $\text{Al}_{1-x}\text{Tb}_x\text{N}$ ($x \approx 0.35$). (e,f) Additional 2D detector images of $\text{Al}_{1-x}\text{Tb}_x\text{N}$ films showing the (e) wz/wz+rs and (f) wz+rs/amorphous boundaries at $x \approx 0.15$ and $x \approx 0.28$ respectively.

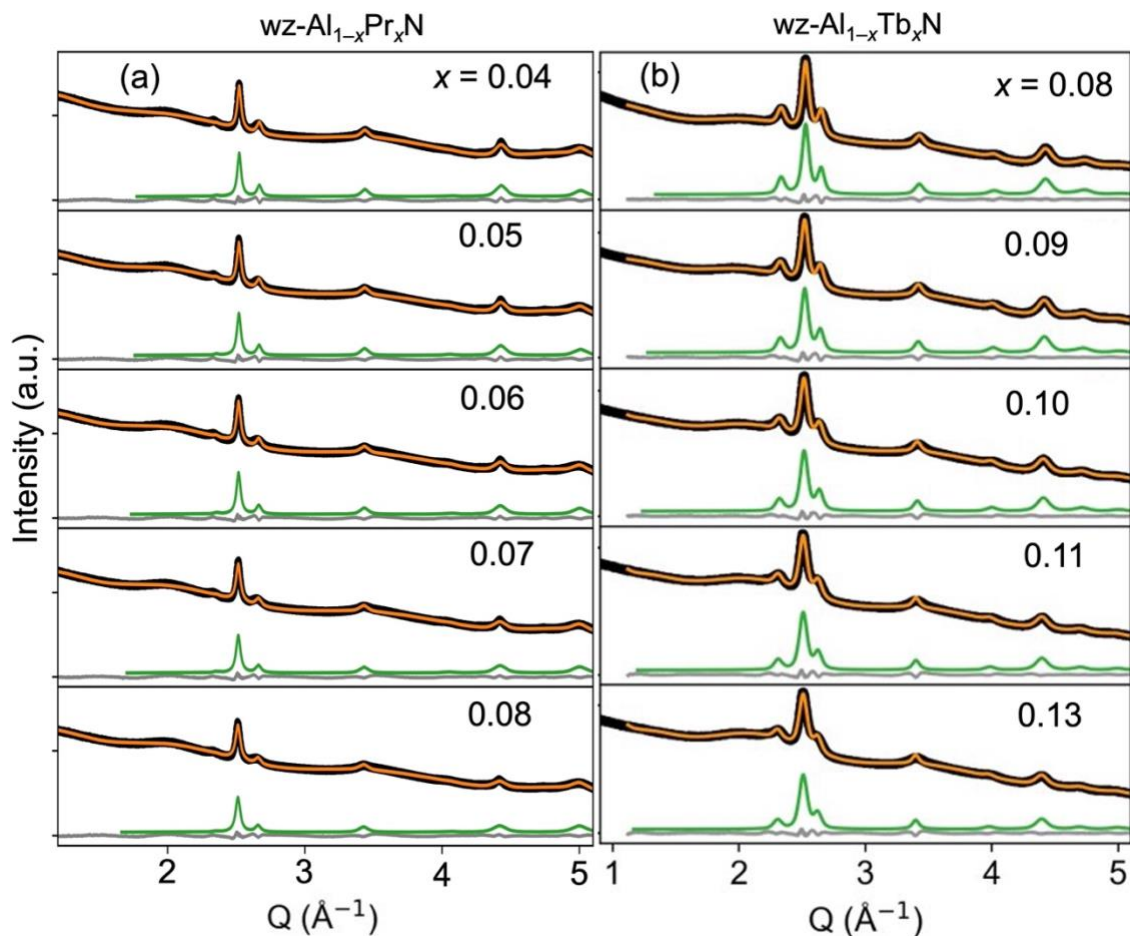


Figure S8: LeBail fits of select GIWAXS data of (a) $\text{Al}_{1-x}\text{Pr}_x\text{N}$ in a phase-pure wurtzite structure with x from 0.04 to 0.08, and (b) $\text{Al}_{1-x}\text{Tb}_x\text{N}$ films in a phase-pure wurtzite structure with up to $x \approx 0.13$. Black dots are data, orange traces show overall fit (phase + background), green traces show the fit component from the wz phase, and the gray trace shows the difference between the data and the overall fit.

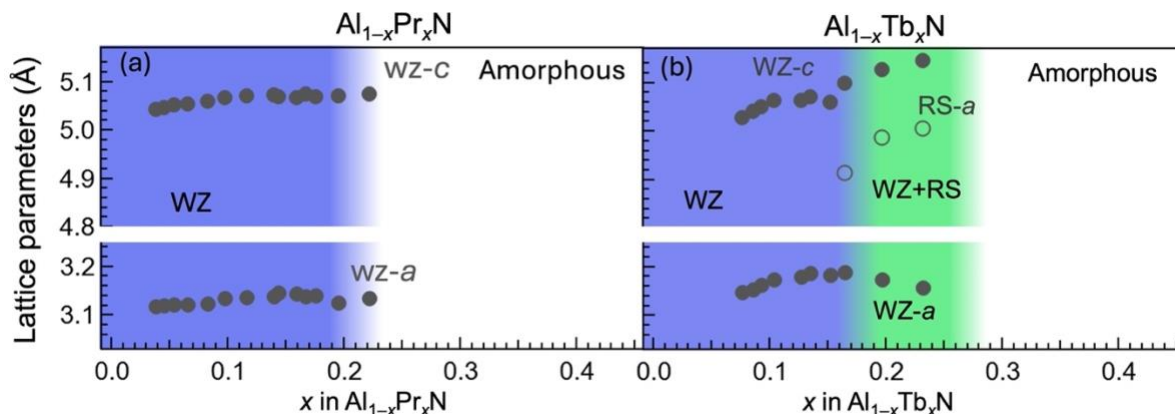


Figure S9: Lattice parameters extracted from LeBail fits of (a) $\text{Al}_{1-x}\text{Pr}_x\text{N}$ films, and (b) $\text{Al}_{1-x}\text{Tb}_x\text{N}$ films. In the phase-pure wurtzite regions of $\text{Al}_{1-x}\text{Pr}_x\text{N}$ (up to $x \approx 0.22$) and $\text{Al}_{1-x}\text{Tb}_x\text{N}$ (up to $x \approx 0.14$), the wurtzite a and c lattice parameters were extracted. In the mixed wz+rs phase region for $\text{Al}_{1-x}\text{Tb}_x\text{N}$ ($0.15 \leq x \leq 0.28$), both the wurtzite a and c lattice parameters and the rocksalt a lattice parameter were extracted.

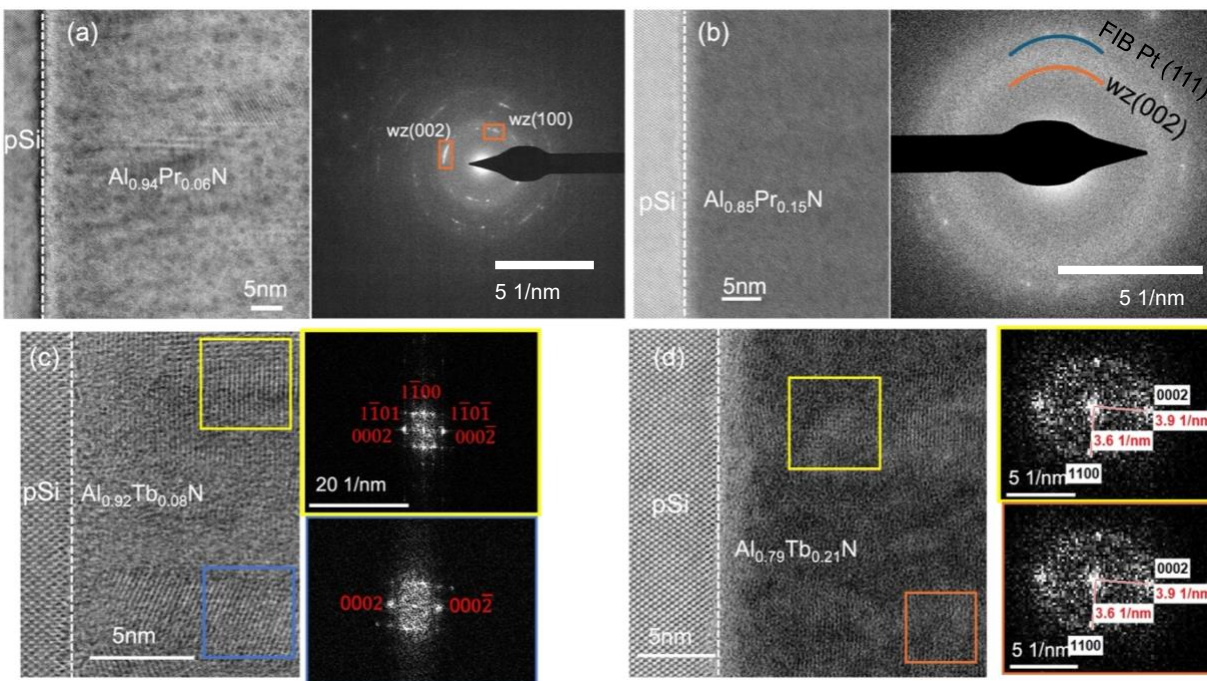


Figure S10: (a,b) STEM-DF images and SAED patterns of $\text{Al}_{1-x}\text{Pr}_x\text{N}$ with (a) $x \approx 0.06$ and (b) $x \approx 0.15$. For $x \approx 0.06$, the SAED shows peaks from the wurtzite phase. For $x \approx 0.15$, the SAED shows a diffuse ring that lines up with the (002) d-spacing of the wurtzite phase. The outer ring denoted by the blue arc arises from the nanocrystalline Pt deposited during the FIB process. (c,d) STEM-BF images and fast Fourier transforms (FFTs) at two different regions of each STEM-BF image of $\text{Al}_{1-x}\text{Tb}_x\text{N}$ with (c) $x = 0.08$ and (d) $x = 0.21$. The FFTs indicate the presence of the wurtzite phase.

Table S2: Reference CL peaks of Pr³⁺ compared with those observed in our measurements.

Transition	Reference Wavelength (nm)	Observed wavelength (nm)
$^3P_0 \rightarrow ^3H_4$	490	—
$^3P_1 \rightarrow ^3H_5$	526	527
$^1D_2 \rightarrow ^3H_4$	603	—
$^3P_0 \rightarrow ^3F_2$	650	654
$^3P_1 \rightarrow ^3F_3$	673	673
$^3P_0 \rightarrow ^3F_3$	694	—
$^1D_2 \rightarrow ^3H_5$	696	—

Table S3: Reference CL peaks of Tb³⁺ compared with those observed in our measurements.

Transition	Reference Wavelength (nm)	Observed wavelength (nm)
$^5D_3 \rightarrow ^7F_6$	384	—
$^5D_3 \rightarrow ^7F_5$	424	—
$^5D_3 \rightarrow ^7F_4$	444	—
$^5D_3 \rightarrow ^7F_3$	463	—
$^5D_3 \rightarrow ^7F_2$	467	—
$^5D_4 \rightarrow ^7F_6$	496	492
$^5D_4 \rightarrow ^7F_5$	551	554
$^5D_4 \rightarrow ^7F_4$	587	589
$^5D_4 \rightarrow ^7F_3$	626	627
$^5D_4 \rightarrow ^7F_2$	660	656